

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ④	18	—	—	V	$V_{GE} = 0V, I_C = 1.0A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.69	—	V/°C	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(ON)}$	Collector-to-Emitter Saturation Voltage	—	1.59	1.8	V	$I_C = 17A, V_{GE} = 15V$
		—	1.99	—		$I_C = 31A, V_{GE} = 15V$
		—	1.7	—		$I_C = 17A, T_J = 150^\circ\text{C}$ See Fig. 2, 5
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-11	—	mV/°C	$V_{CE} = V_{GE}, I_C = 250\mu A$
g_{fe}	Forward Transconductance ⑤	6.1	10	—	S	$V_{CE} = 100V, I_C = 17A$
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	$V_{GE} = 0V, V_{CE} = 600V$
		—	—	2.0		$V_{GE} = 0V, V_{CE} = 10V, T_J = 25^\circ\text{C}$
		—	—	1000		$V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	51	77	nC	$I_C = 17A$
Q_{ge}	Gate - Emitter Charge (turn-on)	—	7.9	12		$V_{CC} = 400V$ See Fig. 8
Q_{gc}	Gate - Collector Charge (turn-on)	—	19	28		$V_{GE} = 15V$
$t_{d(on)}$	Turn-On Delay Time	—	21	—	ns	$T_J = 25^\circ\text{C}$ $I_C = 17A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 23\Omega$ Energy losses include "tail" See Fig. 10, 11, 13, 14
t_r	Rise Time	—	15	—		
$t_{d(off)}$	Turn-Off Delay Time	—	200	300		
t_f	Fall Time	—	180	270		
E_{on}	Turn-On Switching Loss	—	0.23	—	mJ	See Fig. 10, 11, 13, 14
E_{off}	Turn-Off Switching Loss	—	1.18	—		
E_{ts}	Total Switching Loss	—	1.41	2.0		
$t_{d(on)}$	Turn-On Delay Time	—	20	—	ns	$T_J = 150^\circ\text{C}$, $I_C = 17A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 23\Omega$ Energy losses include "tail" See Fig. 13, 14
t_r	Rise Time	—	16	—		
$t_{d(off)}$	Turn-Off Delay Time	—	290	—		
t_f	Fall Time	—	350	—		
E_{ts}	Total Switching Loss	—	2.5	—	mJ	
L_E	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	1100	—	pF	$V_{GE} = 0V$
C_{oes}	Output Capacitance	—	74	—		$V_{CC} = 30V$ See Fig. 7
C_{res}	Reverse Transfer Capacitance	—	14	—		$f = 1.0MHz$

Notes:

- ① Repetitive rating; $V_{GE} = 20V$, pulse width limited by max. junction temperature. (See fig. 13b)
- ② $V_{CC} = 80\%(V_{CES})$, $V_{GE} = 20V$, $L = 10\mu H$, $R_G = 23\Omega$, (See fig. 13a)
- ③ Repetitive rating; pulse width limited by maximum junction temperature.

- ④ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
- ⑤ Pulse width $5.0\mu s$, single shot.

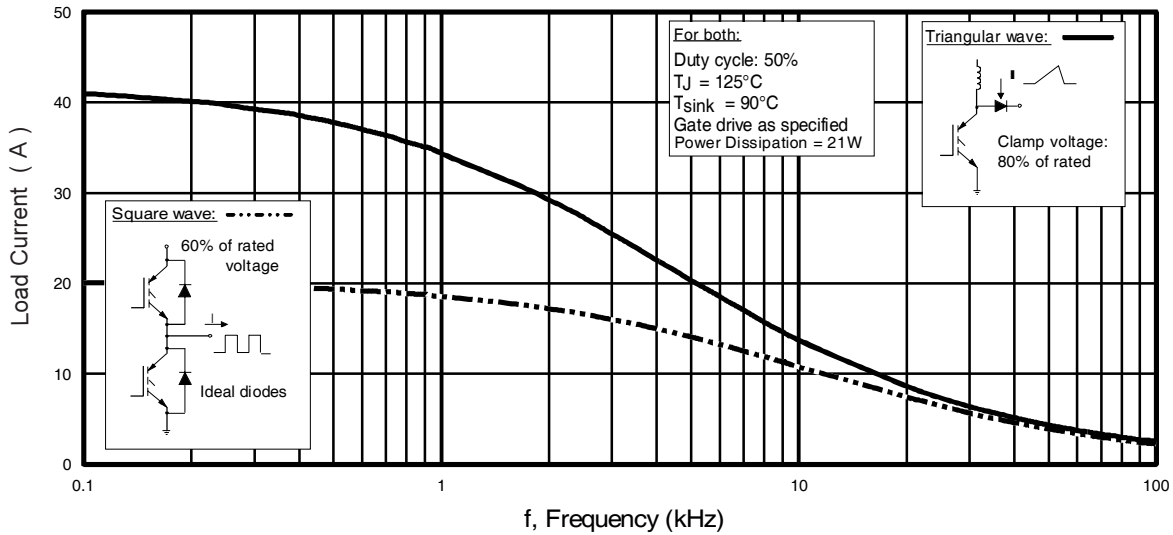


Fig. 1 - Typical Load Current vs. Frequency
(For square wave, $I = I_{RMS}$ of fundamental; for triangular wave, $I = I_{PK}$)

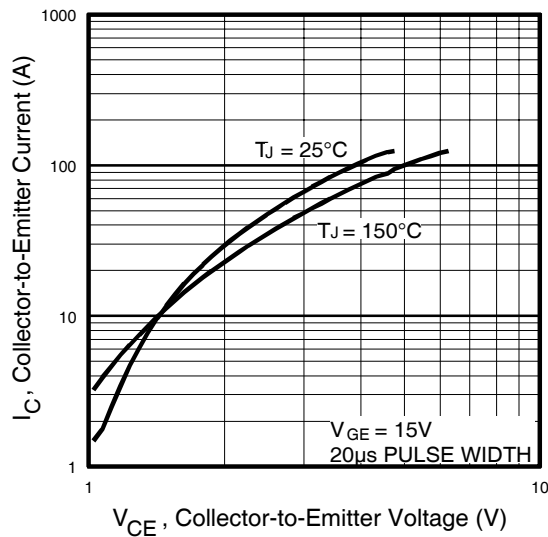


Fig. 2 - Typical Output Characteristics

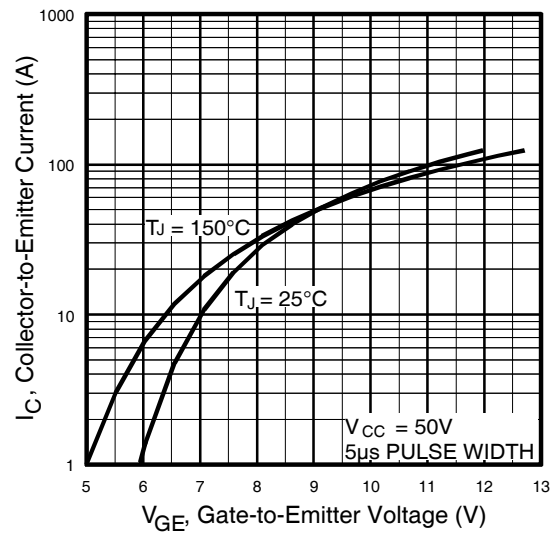


Fig. 3 - Typical Transfer Characteristics

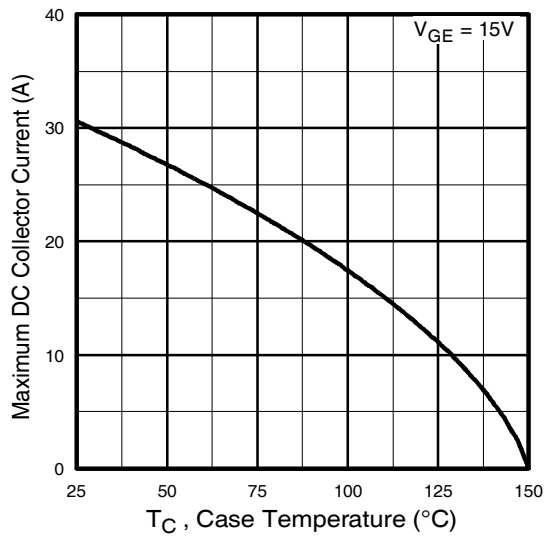


Fig. 4 - Maximum Collector Current vs. Case Temperature

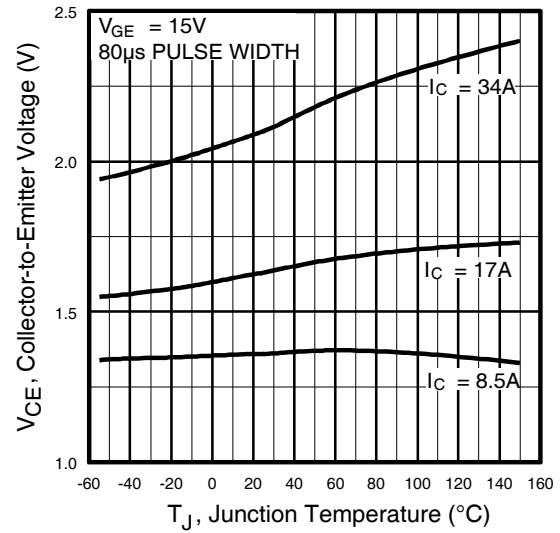


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

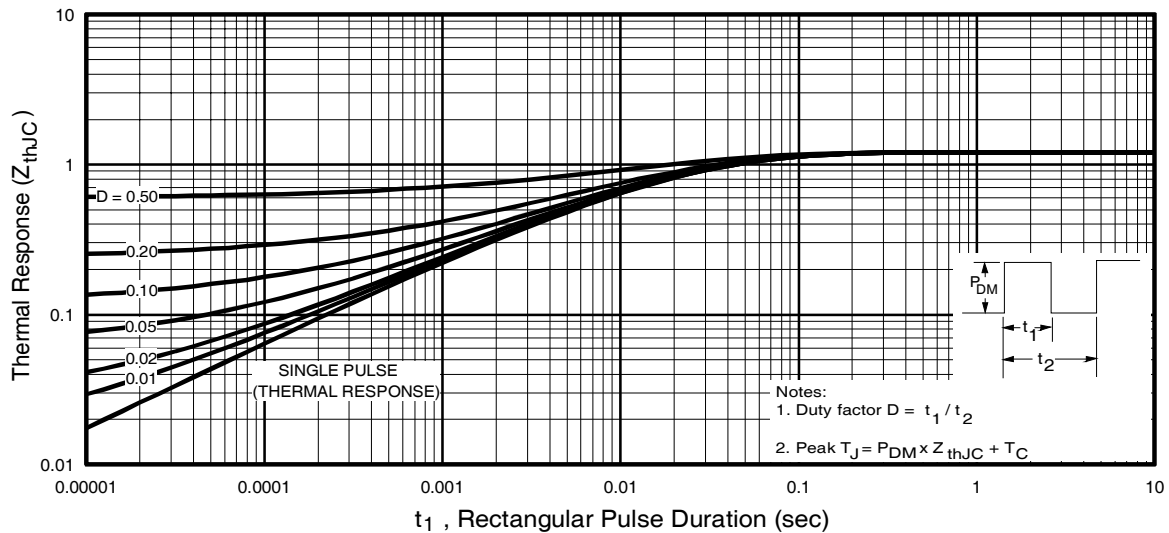


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

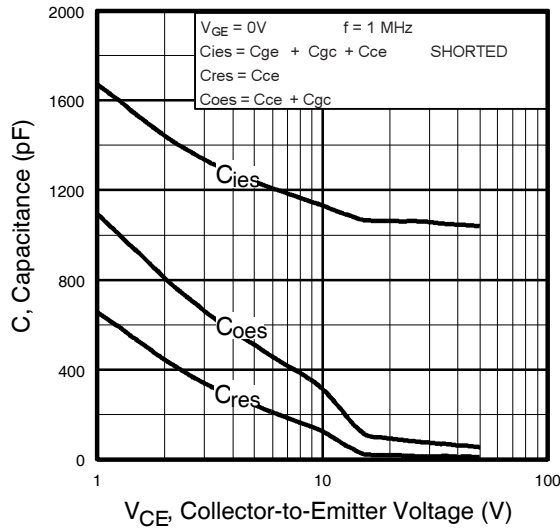


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

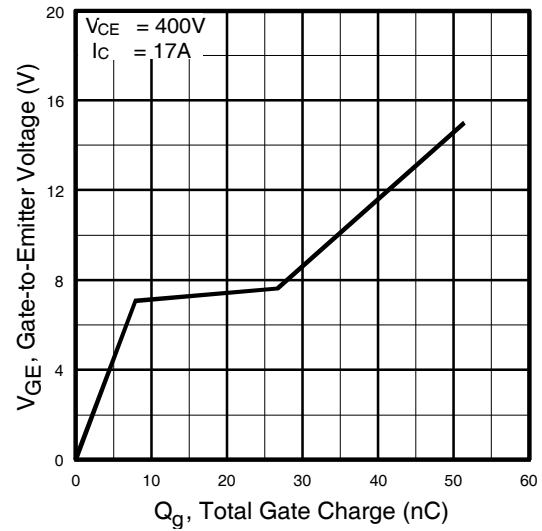


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

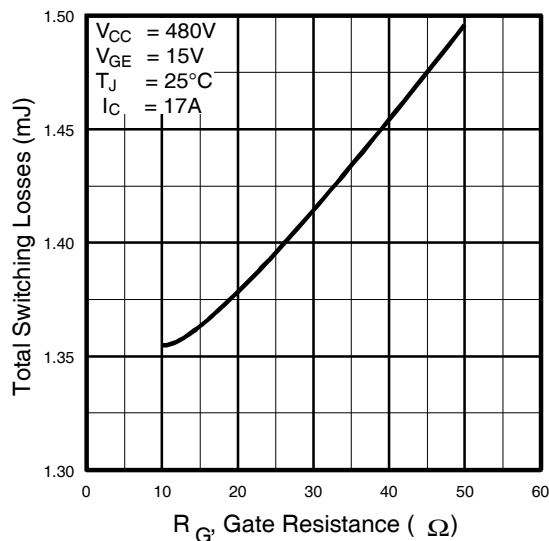


Fig. 9 - Typical Switching Losses vs. Gate Resistance

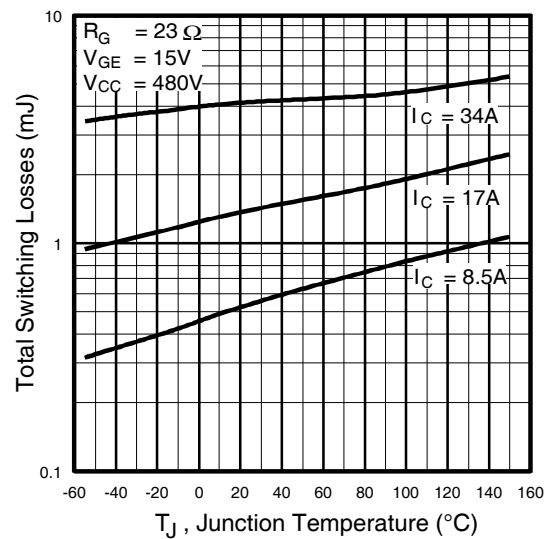


Fig. 10 - Typical Switching Losses vs. Junction Temperature

IRG4BC30FPbF

International
IR Rectifier

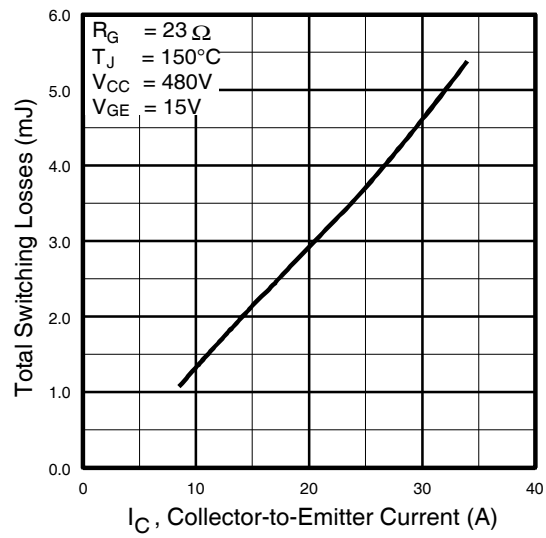


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

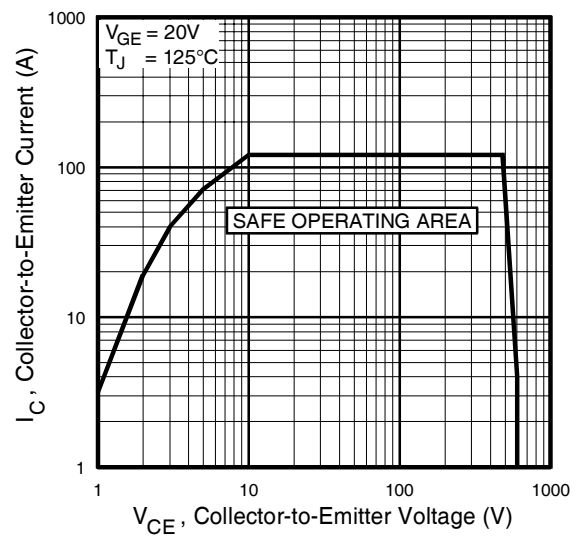


Fig. 12 - Turn-Off SOA

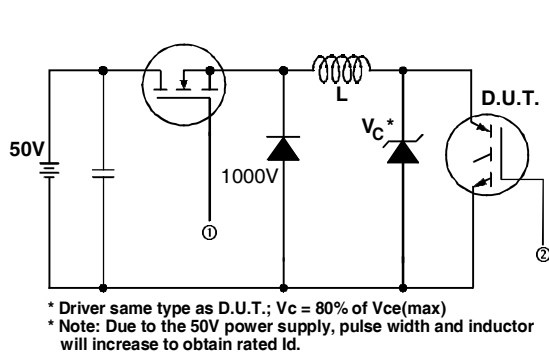


Fig. 13a - Clamped Inductive Load Test Circuit

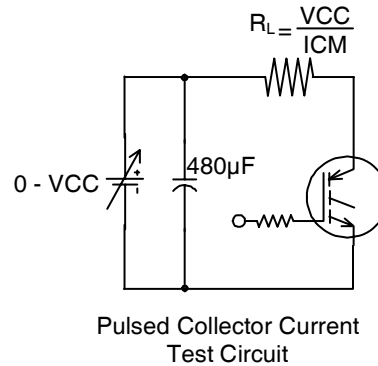


Fig. 13b - Pulsed Collector Current Test Circuit

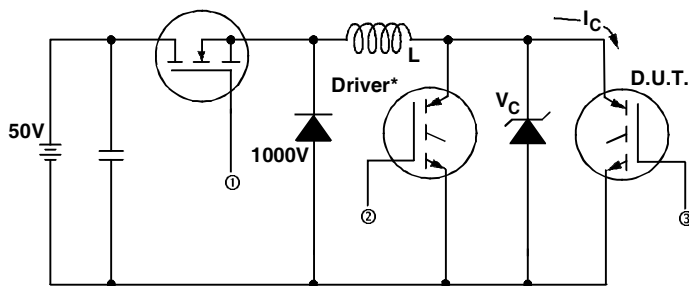


Fig. 14a - Switching Loss Test Circuit

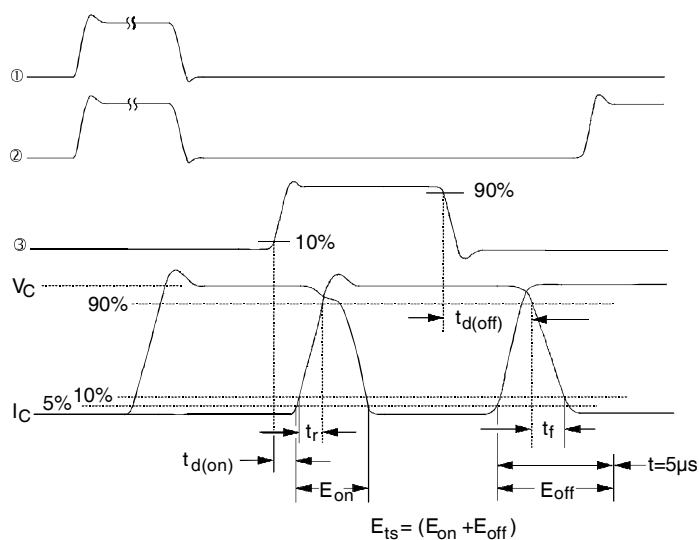
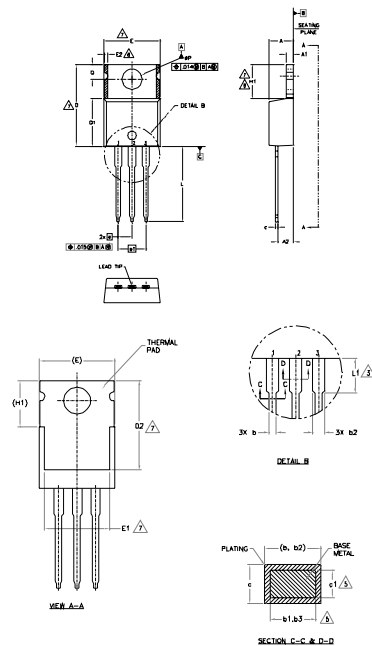


Fig. 14b - Switching Loss Waveforms

TO-220AB Package Outline (Dimensions are shown in millimeters (inches))



- NOTES:
- 1- DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M- 1994.
 - 2- LEAD DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
 - 3- LEAD DIMENSION AND FINISH UNCONTROLLED IN L1
 - 4- DIMENSION D1 OF & E1 DO NOT INCLUDE MOUNTING FLANGE WELD FLASH
 - 5- SMALL PART EXCEEDS 0.0127 (0.500) IN SIZE. THESE DIMENSIONS ARE MEASURED AT THE OUTSIDE SURFACE OF THE PLASTIC BODY.
 - 6- DIMENSION D1, D3 & C1 APPLY TO BARE METAL ONLY.
 - 7- CONTROLLING DIMENSION - INCHES
 - 8- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS L1/2D2 & E1
 - 9- DIMENSION D2 & L1 DETERMINED BY WELD SPATTER REMOVAL AND SINGULARITY IRREGULARITIES ARE ALLOWED.
 - 9- OUTLINE CONFORMS TO JEDEC J-220, EXCEPT (a) (max) and D2 (min) WHERE DIMENSIONS ARE DERIVED FROM THE ACTUAL PAD GEOMETRY.

SYMBOL	DIMENSIONS						NOTE
	MILLIMETERS		INCHES				
	MIN.	MAX.	MIN.	MAX.			
A	3.56	4.83	.140	.190			
A1	0.03	0.92	.001	.035			
A2	0.15	2.92	.006	.115			
b	0.38	1.01	.015	.040			
b1	0.38	0.97	.015	.038		5	
b2	1.14	1.78	.045	.070			
b3	1.14	1.73	.045	.068			
c	0.36	0.56	.014	.022			
D	14.22	16.51	.560	.650		4	
D1	8.38	9.02	.330	.355			
D2	11.68	12.88	.460	.507		7	
E	9.65	10.67	.380	.420		4, 7	
E1	6.86	8.89	.270	.350		7	
E2	—	.076	—	.030		8	
e	2.54	3.81	.100	.150			
e1	—	—	.200	.250			
H1	5.84	6.86	.230	.270		7, 8	
L	12.70	14.53	.500	.580			
LF	5.56	4.06	.140	.160		3	
W	1.54	4.08	.060	.160			
Q	2.54	3.42	.100	.135			

LEAD ASSIGNMENTS

HEWITT

- 1.- GATE
- 2.- BRAN
- 3.- SOURCE

KOTLA, GURPAK

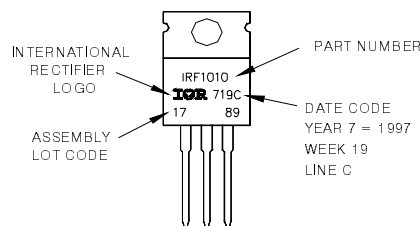
- 1.- GATE
- 2.- COLLECT
- 3.- EMITTER

DIDDIES

- 1.- ANODE
- 2.- CATHODE
- 3.- ANODE

TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF101 0
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE 'C'
Note: "P" in assembly line position indicates "Lead-Free"



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Data and specifications subject to change without notice.

International
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